

- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent Cdv/dt effect decline
- ★ Advanced high cell density Trench technology

Product Summary



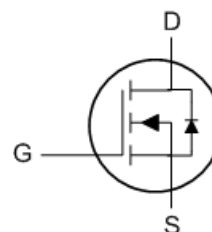
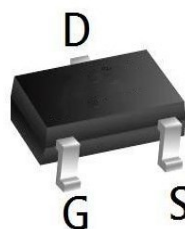
BVDSS	RDSON	ID
100V	95 mΩ	5.0A

Description

The XRS1005L is the high cell density trenched N-ch MOSFETs, which provides excellent RDSON and efficiency for most of the small power switching and load switch applications.

The XRS1005L meet the RoHS and Green Product requirement with full function reliability approved.

SOT23-3L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_A=25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	5	A
$I_D@T_A=70^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	2.2	A
I_{DM}	Pulsed Drain Current ²	11	A
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation ³	1	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	---	125	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	80	$^\circ\text{C/W}$

Electrical Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA	100	110	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 100V, V _{GS} = 0V	-	-	1	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA
On Characteristics ^{note3}						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	1.0	1.95	3.0	V
R _{DS(on)}	Static Drain-Source On-Resistance ^{note2}	V _{GS} = 10V, I _D = 3A	-	95	140	mΩ
Dynamic Characteristics ^{note4}						
C _{iss}	Input Capacitance	V _{DS} = 50V, V _{GS} = 0V, f = 1.0MHz	-	196	-	pF
C _{oss}	Output Capacitance		-	25.9	-	pF
C _{rss}	Reverse Transfer Capacitance		-	21.4	-	pF
Q _g	Total Gate Charge	V _{DS} = 50V, I _D = 3A, V _{GS} = 10V	-	4.3	-	nC
Q _{gs}	Gate-Source Charge		-	3.5	-	nC
Q _{gd}	Gate-Drain(“Miller”) Charge		-	3.1	-	nC
Switching Characteristics ^{note4}						
t _{d(on)}	Turn-On Delay Time	V _{DD} = 50V, I _{DS} =3A R _G = 2Ω, V _{GEN} = 10V	-	14.7	-	ns
t _r	Turn-On Rise Time		-	3.5	-	ns
t _{d(off)}	Turn-Off Delay Time		-	20.9	-	ns
t _f	Turn-Off Fall Time		-	2.7	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current ^{note2}		-	-	5	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	12	A
V _{SD}	Drain to Source Diode Forward Voltage ^{note3}	V _{GS} = 0V, I _S = 3A	-	-	1.3	V
t _{rr}	Body Diode Reverse Recovery Time	V _{GS} = 0V, I _F = 3A, di/dt = 100A/μs	-	32.1	-	ns
Q _{rr}	Body Diode Reverse Recovery Time Charge		-	39.4	-	nC
I _{rrm}	Peak Reverse Recovery Current		-	2.1	-	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. $V_{DD}=50$ V, $R_G=50$ Ω , $L=0.3$ mH, starting $T_J=25$ $^{\circ}\text{C}$

Typical Characteristics

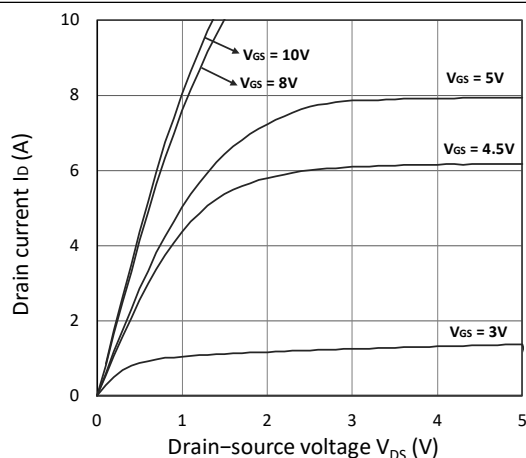


Figure 1. Output Characteristics

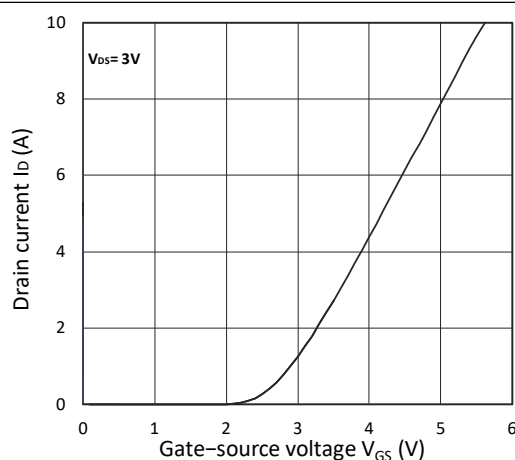


Figure 2. Transfer Characteristics

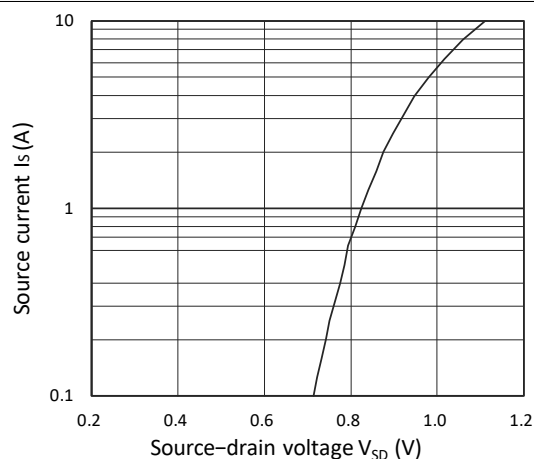


Figure 3. Forward Characteristics of Reverse

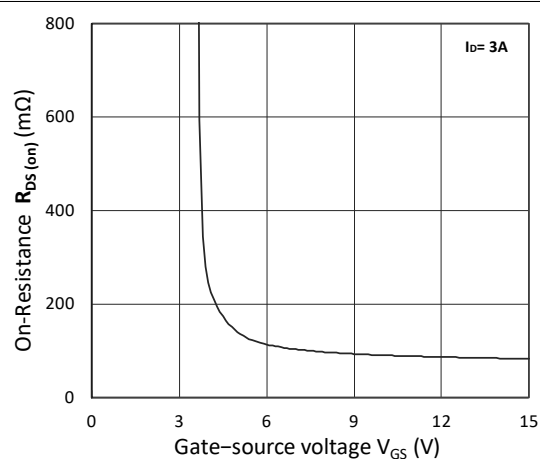


Figure 4. $R_{DS(on)}$ vs. V_{GS}

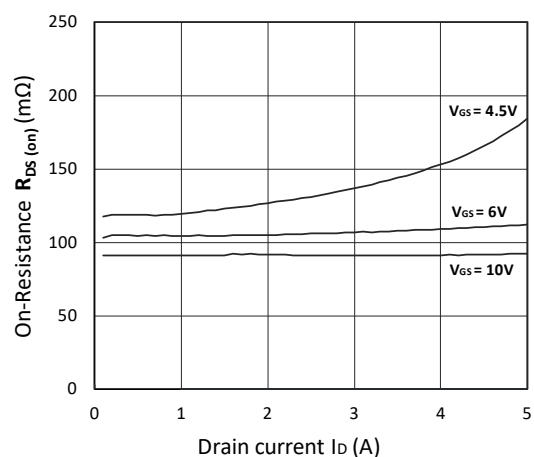


Figure 5. $R_{DS(on)}$ vs. I_D

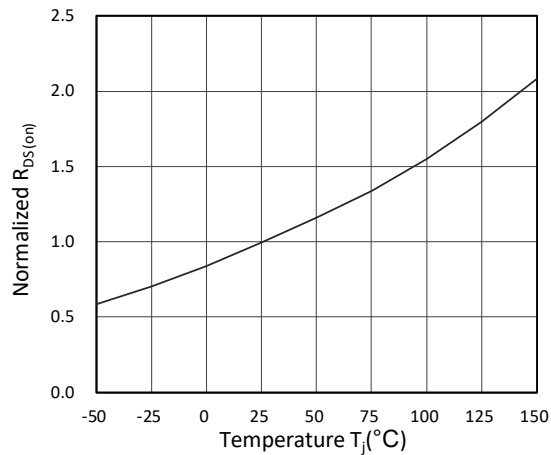


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

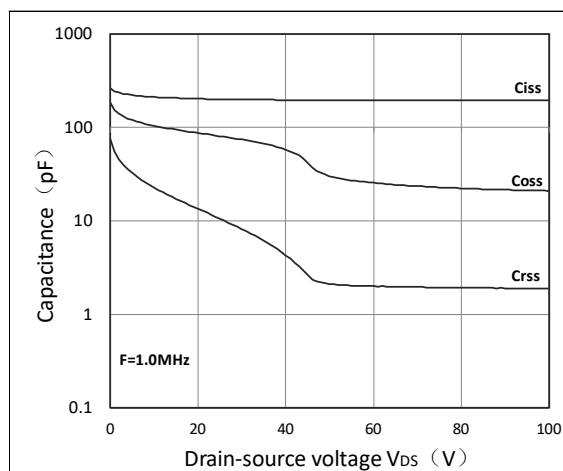


Figure 7. Capacitance Characteristics

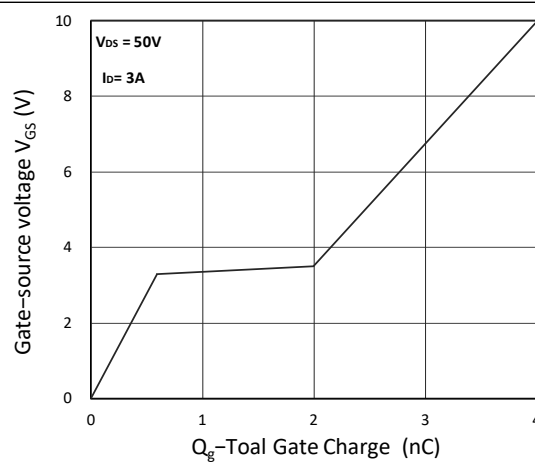
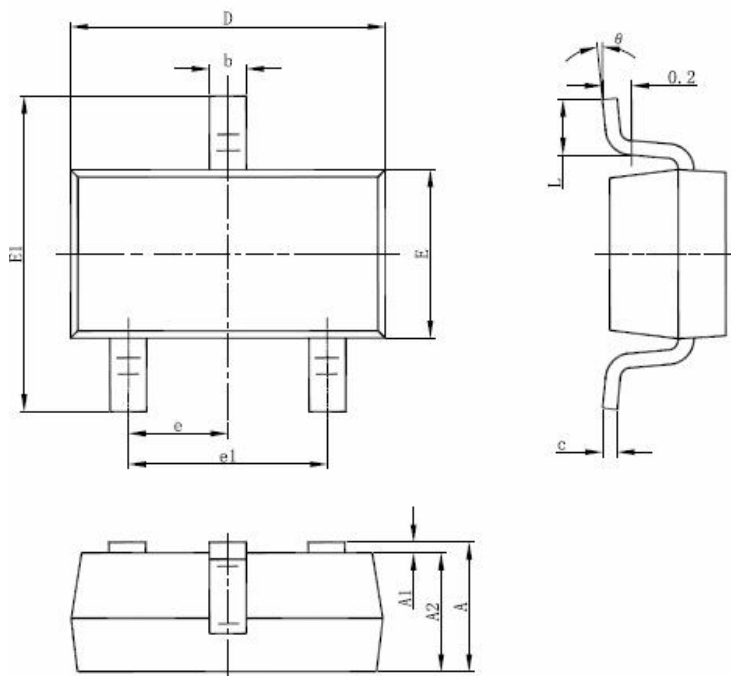


Figure 8. Gate Charge Characteristics

SOT-23-3L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°